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(74) Agents: **TANAI, Sumio** et al.; 2-3-1, Yaesu, Chuo-ku, Tokyo 104-8453 (JP).

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(71) Applicant (for all designated States except US): **TOKYO OHKA KOGYO CO., LTD.** [JP/JP]; 150, Nakamaruko, Nakahara-ku, Kawasaki-shi, Kanagawa 211-0012 (JP).

(72) Inventors; and

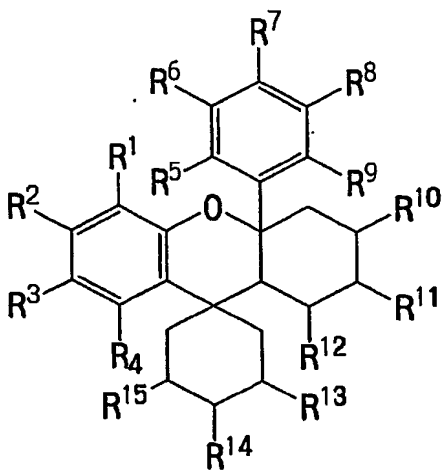
(75) Inventors/Applicants (for US only): **MASUDA, Yasuo** [JP/JP]; c/o Tokyo Ohka Kogyo Co., Ltd., 150, Nakamaruko, Nakahara-ku, Kawasaki-shi, Kanagawa 211-0012 (JP). **OKUI, Toshiki** [JP/JP]; c/o Tokyo Ohka Kogyo

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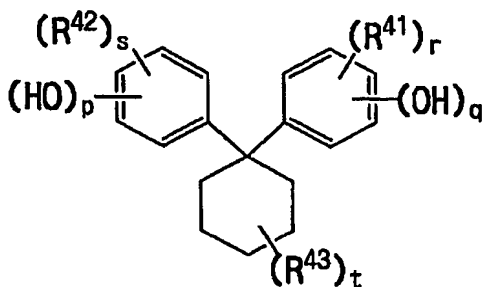
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(54) Title: POSITIVE PHOTORESIST COMPOSITION AND METHOD OF FORMING RESIST PATTERN



... (b-1)

(57) Abstract: There is provided a positive photoresist composition capable of forming a pattern with excellent resolution, excellent resistance to reflection off the substrate, and excellent perpendicularity. The positive photoresist composition comprises (A) an alkali-soluble novolak resin in which a portion of the hydrogen atoms of all the phenolic hydroxyl groups are substituted with 1,2-naphthoquinonediazidesulfonyl groups, and (B) a dissolution promoter represented by a general formula (b-1) and/or a general formula (b-11) shown below.



... (b-11)



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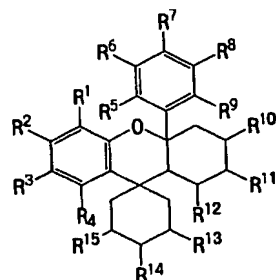
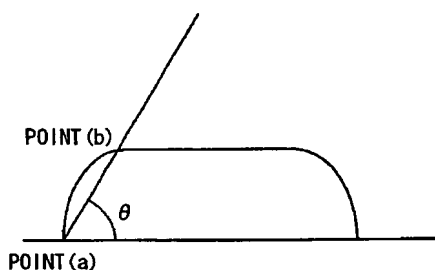
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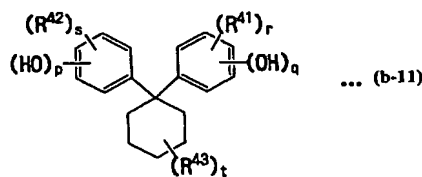
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